

CS8312

IGBT Ignition Predriver with Dynamic Current Regulation

The CS8312 is a bipolar microprocessor interface IC designed to drive an IGBT (or logic level MOSFETs) powering large inductive loads in harsh operating environments. The IC's dynamic current limit function lets the microprocessor adjust the current limit threshold to the real time needs of the system.

CLI, the current limit input, sets the current limit for the IGBT high or low as directed by the system microprocessor. CLI also raises and lowers the threshold on the diagnostic FLAG output signal. The FLAG output signals the microprocessor when the current level approaches current limit on the IGBT. The CTRL input enables the FLAG function.

Features

- μ P Compatible Inputs
- Adjustable Current Limit Thresholds
- External Sense Resistor
- Flag Signal to Indicate Output Status

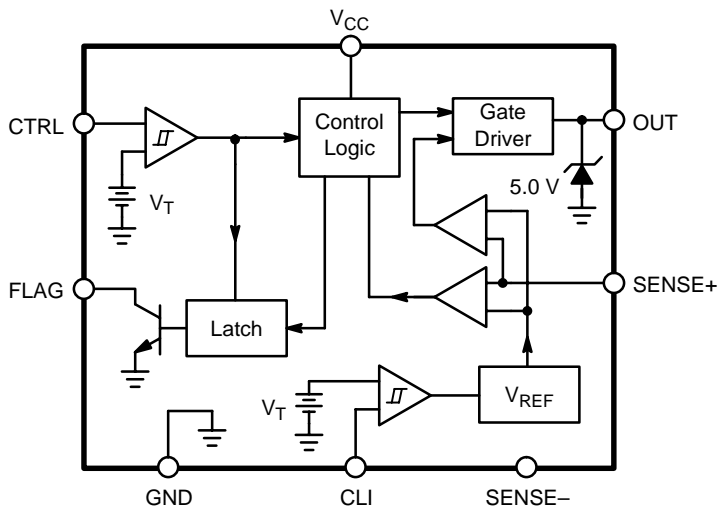
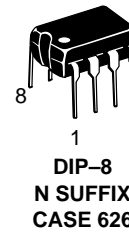


Figure 1. Block Diagram

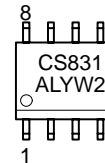
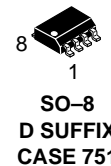
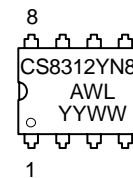


ON Semiconductor™

<http://onsemi.com>

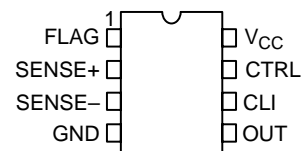


MARKING DIAGRAMS



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week

PIN CONNECTIONS



ORDERING INFORMATION

Device	Package	Shipping
CS8312YN8	DIP-8	50 Units/Rail
CS8312YD8	SO-8	95 Units/Rail
CS8312YDR8	SO-8	2500 Tape & Reel

ABSOLUTE MAXIMUM RATINGS*

Rating	Value	Unit
Supply Voltage	-0.3 to 12	V
Digital Input Currents	2.0	mA
Internal Power Dissipation ($T_A = 25^\circ\text{C}$)	700	mW
Junction Temperature Range	-40 to +150	$^\circ\text{C}$
Storage Temperature Range	-55 to +165	$^\circ\text{C}$
Electrostatic Discharge (Human Body Model)	2.0	kV
Lead Temperature Soldering	Wave Solder (through hole styles only) Note 1. Reflow (SMD styles only) Note 2.	260 peak 230 peak $^\circ\text{C}$ $^\circ\text{C}$

1. 10 seconds max.

2. 60 seconds max above 183°C

*The maximum package power dissipation must be observed.

ELECTRICAL CHARACTERISTICS ($7.0\text{ V} \leq V_{CC} \leq 10\text{ V}$, $-40^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$,
 $-0.2\text{ V} \leq \text{Differential Ground Voltage} \leq 0.8\text{ V}$; unless otherwise specified.)

Characteristic	Test Conditions	Min	Typ	Max	Unit
General					
Power Supply Including Ripple Voltage	–	7.0	–	10	V
Supply Ripple Frequency	–	10	–	60	kHz
Differential Ground Frequency	–	10	–	60	kHz
Quiescent Current, I_Q					
Turn On	$V_{CTRL} = 5.5\text{ V}$	–	–	15	mA
Turn Off	$V_{CTRL} = -0.3\text{ V}$	–	–	5.0	mA
Supply Voltage Rejection	$V_{CTRL} = 5.5\text{ V}$	30	–	–	dB
Differential Ground Rejection Ratio	$V_{CTRL} = 5.5\text{ V}$	30	–	–	dB
Differential Ground Current Ratio	$V_{CTRL} = -0.3\text{ V}$, ($V_{SENSE-} - V_{GND}$)DC = 1.0 V ($V_{SENSE-} - V_{GND}$)AC = 0.6 V	–	–	3.0	mA
Unity Gain Bandwidth	$V_{CTRL} = 5.5\text{ V}$	400	–	–	kHz
Turn On Delay	CTRL Increasing	–	–	30	μs
Turn Off Delay	CTRL Decreasing	–	–	30	μs

Control Function

Input Voltage Range	$I_{CTRL} = 2.0\text{ mA}$	-0.3	–	5.5	V
Input Threshold					
Turn On	CTRL Increasing	–	–	3.5	V
Turn Off	CTRL Decreasing	1.5	–	–	V
Hysteresis		0.4	–	2.0	V
Voltage	$I_{CTRL} = 10\ \mu\text{A max}$	–	–	1.1	V
Input Capacitance	–	–	–	50	pF

Current Limit Increase Function

Input Voltage Range	$I_{CTRL} = 2.0\text{ mA}$	-0.3	–	5.5	V
Input Threshold					
Turn On	CLI Increasing	–	–	3.5	V
Turn Off	CLI Decreasing	1.5	–	–	V
Hysteresis		0.4	–	2.0	V
Voltage	$I_{CLI} = 10\ \mu\text{A max}$	–	–	1.1	V

CS8312

ELECTRICAL CHARACTERISTICS (continued) ($7.0\text{ V} \leq V_{CC} \leq 10\text{ V}$, $-40^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$, $-0.2\text{ V} \leq \text{Differential Ground Voltage} \leq 0.8\text{ V}$; unless otherwise specified.)

Characteristic	Test Conditions	Min	Typ	Max	Unit
----------------	-----------------	-----	-----	-----	------

Current Limit Increase Function (continued)

Input Capacitance	–	–	–	50	pF
-------------------	---	---	---	----	----

Output Stage

I_{OUT}	–	–	–	5.0	mA
Clamp Voltage	$V_{CTRL} = 5.5\text{ V}$, $I_{OUT} = 1.0\text{ mA}$	4.0	–	5.5	V
Output Off Voltage	$V_{CTRL} = -0.3\text{ V}$, $I_{OUT} = 10\text{ }\mu\text{A}$ $V_{CTRL} = -0.3\text{ V}$, $I_{OUT} = 200\text{ }\mu\text{A}$	–	–	0.5 1.2	V V

Flag Function

Output Low	$V_{CTRL} = 5.5\text{ V}$, $I_{FLAG} = 1.5\text{ mA}$	–	–	0.9	V
Leakage Current	$V_{CTRL} = -0.3\text{ V}$	–	–	10	μA
Output Capacitance	–	–	–	50	pF
Turn On ($V_{SENSE+} - V_{SENSE-}$)	$V_{CTRL} = 5.5\text{ V}$, $V_{CLI} = -0.3\text{ V}$ $V_{CTRL} = 5.5\text{ V}$, $V_{CLI} = 5.5\text{ V}$	210 300	225 –	240 350	mV mV
Turn Off Delay	CTRL Decreasing	–	–	10	μs
Turn On Delay	–	–	–	10	μs
Disable Time	–	100	–	450	μs

Sense Function

Input Voltage Range	–	-0.3	–	2.5	V
Sense Regulation Voltage	$V_{CTRL} = 5.5\text{ V}$, $V_{CLI} = -0.3\text{ V}$ $V_{CTRL} = 5.5\text{ V}$, $V_{CLI} = 5.5\text{ V}$	270 380	295 410	320 440	mV mV
Input Leakage Current	$V_{CTRL} = 5.5\text{ V}$	–	–	5.0	μA
Propagation Delay	$V_{CTRL} = 5.5\text{ V}$	–	–	20	μs

PACKAGE PIN DESCRIPTION

PACKAGE PIN #		PIN SYMBOL	FUNCTION
DIP-8	SO-8		
1	1	FLAG	Indicates whether current through the IGBT has reached a pre-set level.
2	2	SENSE+	Positive input to current comparator.
3	3	SENSE-	Ground (SENSE-) for current sense resistor.
4	4	GND	Ground connection.
5	5	OUT	Output voltage to IGBT (MOSFET) gate.
6	6	CLI	Current limit input increase.
7	7	CTRL	Control input.
8	8	V_{CC}	Supply voltage.

CS8312

CIRCUIT DESCRIPTION

Flag Function (See Figure 2)

The flag indicates when the voltage across the two sense pins is approaching a current limit level that has been determined by the value of the external sense resistor (R_{SENSE}) and the state of the CTRL and CLI pins. If the voltage across the sense pins ($SENSE+$, $SENSE-$) is less than the flag turn-on voltage, then the FLAG is off. When the voltage between the sense pins equals the FLAG turn on voltage, the FLAG will latch on until the CTRL pin goes low. FLAG is disabled whenever CTRL is low. Changing the CLI pin from low to high will increase nominal FLAG turn on voltage by approximately 45%.

Table 1. FLAG Timing Sequence

State	CONTROL	SENSE+	FLAG
0	Low	X	OFF
1	High	Below Threshold	OFF
2	High	Above Threshold	ON
3	High	X	ON
0	Low	X	OFF

Output Stage

The CS8312 output (OUT) saturates and supplies voltage to the IGBT (or MOSFET) gate once the CTRL switches from low to high. As current through the IGBT (MOSFET) increases and the voltage across the sense resistor passes the flag turn on voltage, the FLAG will turn on. If the current through the sense resistor continues to rise and the sense resistor voltage reaches the regulation sense voltage, then the gate voltage will fall to a level that regulates the driver and maintains the regulation sense voltage at the sense resistor.

Current Limit Function

Changing the CLI pin from a logic low to a logic high increases the FLAG turn on voltage by approximately 45% and the regulation sense voltage by approximately 39% respectively.

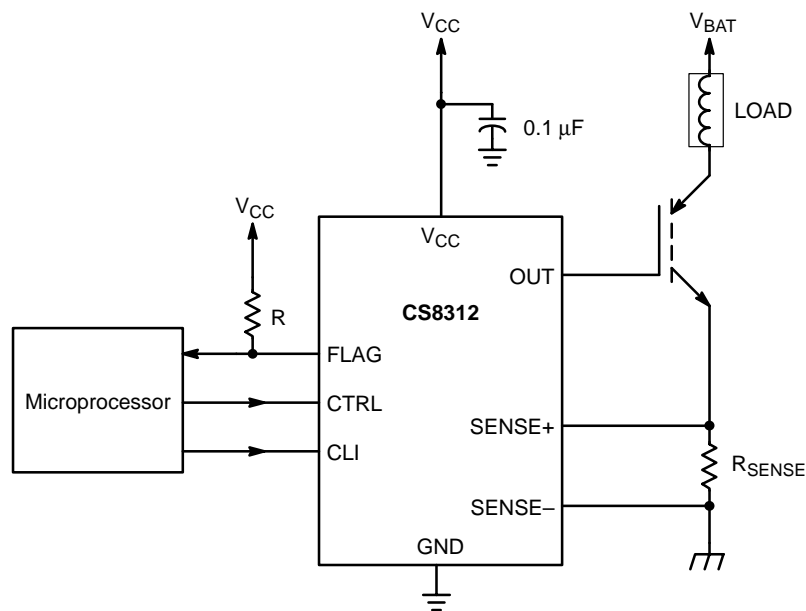


Figure 2. Application and Test Diagram

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

PDIP-8
CASE 626-05
ISSUE P

DATE 22 APR 2015



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	----	0.210	----	5.33
A1	0.015	----	0.38	----
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
C	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005	----	0.13	----
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
eB	----	0.430	----	10.92
L	0.115	0.150	2.92	3.81
M	----	10°	----	10°

GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- STYLE 1:
PIN 1. AC IN
2. DC + IN
3. DC - IN
4. AC IN
5. GROUND
6. OUTPUT
7. AUXILIARY
8. V_{CC}

DOCUMENT NUMBER:	98ASB42420B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	PDIP-8	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC MARKING DIAGRAM*



SCALE 6:1 ($\frac{\text{mm}}{\text{inches}}$)



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-8 NB	PAGE 1 OF 2

onsemi and ONsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

- | | | | |
|---|--|--|--|
| <p>STYLE 1:
 PIN 1. EMITTER
 2. COLLECTOR
 3. COLLECTOR
 4. EMITTER
 5. EMITTER
 6. BASE
 7. BASE
 8. EMITTER</p> | <p>STYLE 2:
 PIN 1. COLLECTOR, DIE, #1
 2. COLLECTOR, #1
 3. COLLECTOR, #2
 4. COLLECTOR, #2
 5. BASE, #2
 6. EMITTER, #2
 7. BASE, #1
 8. EMITTER, #1</p> | <p>STYLE 3:
 PIN 1. DRAIN, DIE #1
 2. DRAIN, #1
 3. DRAIN, #2
 4. DRAIN, #2
 5. GATE, #2
 6. SOURCE, #2
 7. GATE, #1
 8. SOURCE, #1</p> | <p>STYLE 4:
 PIN 1. ANODE
 2. ANODE
 3. ANODE
 4. ANODE
 5. ANODE
 6. ANODE
 7. ANODE
 8. COMMON CATHODE</p> |
| <p>STYLE 5:
 PIN 1. DRAIN
 2. DRAIN
 3. DRAIN
 4. DRAIN
 5. GATE
 6. GATE
 7. SOURCE
 8. SOURCE</p> | <p>STYLE 6:
 PIN 1. SOURCE
 2. DRAIN
 3. DRAIN
 4. SOURCE
 5. SOURCE
 6. GATE
 7. GATE
 8. SOURCE</p> | <p>STYLE 7:
 PIN 1. INPUT
 2. EXTERNAL BYPASS
 3. THIRD STAGE SOURCE
 4. GROUND
 5. DRAIN
 6. GATE 3
 7. SECOND STAGE Vd
 8. FIRST STAGE Vd</p> | <p>STYLE 8:
 PIN 1. COLLECTOR, DIE #1
 2. BASE, #1
 3. BASE, #2
 4. COLLECTOR, #2
 5. COLLECTOR, #2
 6. EMITTER, #2
 7. EMITTER, #1
 8. COLLECTOR, #1</p> |
| <p>STYLE 9:
 PIN 1. EMITTER, COMMON
 2. COLLECTOR, DIE #1
 3. COLLECTOR, DIE #2
 4. EMITTER, COMMON
 5. EMITTER, COMMON
 6. BASE, DIE #2
 7. BASE, DIE #1
 8. EMITTER, COMMON</p> | <p>STYLE 10:
 PIN 1. GROUND
 2. BIAS 1
 3. OUTPUT
 4. GROUND
 5. GROUND
 6. BIAS 2
 7. INPUT
 8. GROUND</p> | <p>STYLE 11:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. DRAIN 2
 7. DRAIN 1
 8. DRAIN 1</p> | <p>STYLE 12:
 PIN 1. SOURCE
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 13:
 PIN 1. N.C.
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> | <p>STYLE 14:
 PIN 1. N-SOURCE
 2. N-GATE
 3. P-SOURCE
 4. P-GATE
 5. P-DRAIN
 6. P-DRAIN
 7. N-DRAIN
 8. N-DRAIN</p> | <p>STYLE 15:
 PIN 1. ANODE 1
 2. ANODE 1
 3. ANODE 1
 4. ANODE 1
 5. CATHODE, COMMON
 6. CATHODE, COMMON
 7. CATHODE, COMMON
 8. CATHODE, COMMON</p> | <p>STYLE 16:
 PIN 1. EMITTER, DIE #1
 2. BASE, DIE #1
 3. EMITTER, DIE #2
 4. BASE, DIE #2
 5. COLLECTOR, DIE #2
 6. COLLECTOR, DIE #2
 7. COLLECTOR, DIE #1
 8. COLLECTOR, DIE #1</p> |
| <p>STYLE 17:
 PIN 1. VCC
 2. V2OUT
 3. V1OUT
 4. TXE
 5. RXE
 6. VEE
 7. GND
 8. ACC</p> | <p>STYLE 18:
 PIN 1. ANODE
 2. ANODE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. CATHODE
 8. CATHODE</p> | <p>STYLE 19:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. MIRROR 2
 7. DRAIN 1
 8. MIRROR 1</p> | <p>STYLE 20:
 PIN 1. SOURCE (N)
 2. GATE (N)
 3. SOURCE (P)
 4. GATE (P)
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 21:
 PIN 1. CATHODE 1
 2. CATHODE 2
 3. CATHODE 3
 4. CATHODE 4
 5. CATHODE 5
 6. COMMON ANODE
 7. COMMON ANODE
 8. CATHODE 6</p> | <p>STYLE 22:
 PIN 1. I/O LINE 1
 2. COMMON CATHODE/VCC
 3. COMMON CATHODE/VCC
 4. I/O LINE 3
 5. COMMON ANODE/GND
 6. I/O LINE 4
 7. I/O LINE 5
 8. COMMON ANODE/GND</p> | <p>STYLE 23:
 PIN 1. LINE 1 IN
 2. COMMON ANODE/GND
 3. COMMON ANODE/GND
 4. LINE 2 IN
 5. LINE 2 OUT
 6. COMMON ANODE/GND
 7. COMMON ANODE/GND
 8. LINE 1 OUT</p> | <p>STYLE 24:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR/ANODE
 4. COLLECTOR/ANODE
 5. CATHODE
 6. CATHODE
 7. COLLECTOR/ANODE
 8. COLLECTOR/ANODE</p> |
| <p>STYLE 25:
 PIN 1. VIN
 2. N/C
 3. REXT
 4. GND
 5. IOUT
 6. IOUT
 7. IOUT
 8. IOUT</p> | <p>STYLE 26:
 PIN 1. GND
 2. dv/dt
 3. ENABLE
 4. ILIMIT
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. VCC</p> | <p>STYLE 27:
 PIN 1. ILIMIT
 2. OVLO
 3. UVLO
 4. INPUT+
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. DRAIN</p> | <p>STYLE 28:
 PIN 1. SW_TO_GND
 2. DASIC_OFF
 3. DASIC_SW_DET
 4. GND
 5. V_MON
 6. VBULK
 7. VBULK
 8. VIN</p> |
| <p>STYLE 29:
 PIN 1. BASE, DIE #1
 2. EMITTER, #1
 3. BASE, #2
 4. EMITTER, #2
 5. COLLECTOR, #2
 6. COLLECTOR, #2
 7. COLLECTOR, #1
 8. COLLECTOR, #1</p> | <p>STYLE 30:
 PIN 1. DRAIN 1
 2. DRAIN 1
 3. GATE 2
 4. SOURCE 2
 5. SOURCE 1/DRAIN 2
 6. SOURCE 1/DRAIN 2
 7. SOURCE 1/DRAIN 2
 8. GATE 1</p> | | |

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-8 NB	PAGE 2 OF 2

onsemi and **ONSEMI** are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales